

# Yun Zhang

## List of Publications by Year in descending order

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20  
papers

637  
citations

759233

12  
h-index

839539

18  
g-index

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all docs

20  
docs citations

20  
times ranked

777  
citing authors

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 1  | Semi-polar (11 $\bar{1}2$ ) AlN epitaxial films on m-plane sapphire substrates with greatly improved crystalline quality obtained by high-temperature annealing. Journal of Crystal Growth, 2021, 570, 126207.  | 1.5 | 6         |
| 2  | Optimization of selective-area regrown n-GaN via MOCVD for high-frequency HEMT. Applied Physics Letters, 2021, 119, .   | 3.3 | 8         |
| 3  | Structural characterization of AlN (11-22) films prepared by sputtering and thermal annealing on m-plane sapphire substrates. Superlattices and Microstructures, 2020, 141, 106493.                             | 3.1 | 9         |
| 4  | Method of the out-of-band rejection improvement of the AlN based surface acoustic wave filters. Ultrasonics, 2019, 91, 30-33.   | 3.9 | 10        |
| 5  | AlGaIn-based ultraviolet light-emitting diode on high-temperature annealed sputtered AlN template. Journal of Alloys and Compounds, 2019, 794, 8-12.  | 5.5 | 32        |
| 6  | Enhanced performance of AlN SAW devices with wave propagation along the $\Gamma$ -K direction on c-plane sapphire substrate. Journal Physics D: Applied Physics, 2019, 52, 215103.                              | 2.8 | 14        |
| 7  | Reducing stimulated emission threshold power density of AlGaIn/AlN multiple quantum wells by nano-trench-patterned AlN template. Journal of Alloys and Compounds, 2019, 777, 344-349.                           | 5.5 | 13        |
| 8  | Integrated High-Q Crystalline AlN Microresonators for Broadband Kerr and Raman Frequency Combs. ACS Photonics, 2018, 5, 1943-1950.  | 6.6 | 71        |
| 9  | AlGaIn-based ultraviolet light-emitting diodes on sputter-deposited AlN templates with epitaxial AlN/AlGaIn superlattices. Superlattices and Microstructures, 2018, 113, 713-719.                               | 3.1 | 10        |
| 10 | Generation of multiple near-visible comb lines in an AlN microring via $\chi^{(2)}$ and $\chi^{(3)}$ optical nonlinearities. Applied Physics Letters, 2018, 113, .  | 3.3 | 25        |
| 11 | Crystal quality improvement of sputtered AlN film on sapphire substrate by high-temperature annealing. Journal of Materials Science: Materials in Electronics, 2018, 29, 13766-13773.                           | 2.2 | 29        |
| 12 | Deep-ultraviolet stimulated emission from AlGaIn/AlN multiple-quantum-wells on nano-patterned AlN/sapphire templates with reduced threshold power density. Journal of Alloys and Compounds, 2017, 723, 192-196. | 5.5 | 10        |
| 13 | Integrated continuous-wave aluminum nitride Raman laser. Optica, 2017, 4, 893.  | 9.3 | 54        |
| 14 | Aluminum nitride-on-sapphire platform for integrated high-Q microresonators. Optics Express, 2017, 25, 587.   | 3.4 | 48        |
| 15 | Broadband visible comb generation in AlN-on-sapphire microresonators. , 2017, , .   |     | 1         |
| 16 | Stimulated emission at 272 nm from an Al <sub>x</sub> Ga <sub>1-x</sub> N-based multiple-quantum-well laser with two-step etched facets. RSC Advances, 2016, 6, 50245-50249.                                    | 3.6 | 14        |
| 17 | Broadband tunable microwave photonic phase shifter with low RF power variation in a high-Q AlN microring. Optics Letters, 2016, 41, 3599.   | 3.3 | 31        |
| 18 | High-resistance GaN-based buffer layers grown by a polarization doping method. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 307-310.   | 0.8 | 0         |

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 19 | AlGaN-based deep ultraviolet light-emitting diodes grown on nano-patterned sapphire substrates with significant improvement in internal quantum efficiency. <i>Journal of Crystal Growth</i> , 2014, 395, 9-13. | 1.5 | 68        |
| 20 | 282-nm AlGaN-based deep ultraviolet light-emitting diodes with improved performance on nano-patterned sapphire substrates. <i>Applied Physics Letters</i> , 2013, 102, .  | 3.3 | 184       |